

DESCRIPTION

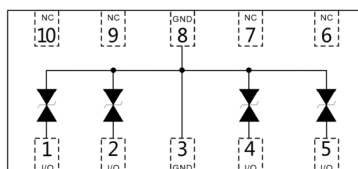
GESD2404JDOC is a four channels low capacitance Bi-directional ESD protection array, GESD2404JDOC is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD) Level 4(±15KV air, ±8KV contact discharge), IEC61000-4-4(electrical fast transient-EFT) (40A,5/50ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

GESD2404JDOC uses ultra-small DFN2510 package. Each GESD2404JDOC device can protect four high-speed data lines. The combined features of low capacitance, ultra-small size and high ESD robustness make GESD2404JDOC ideal for high-speed data ports and high-frequency line applications. The low clamping voltage of the GESD2404JDOC guarantees a minimum stress on the protected IC.

ORDERING INFORMATION

- ✧ Device: GESD2404JDOC
- ✧ Package: DFN2510
- ✧ Marking: 2404OC
- ✧ Material: Halogen free& RoHS compliant
- ✧ Packing: Tape & Reel
- ✧ Quantity per reel: 3,000pcs

PIN CONFIGURATION



FEATURES

- ✧ Transient protection for high-speed data lines
 - IEC 61000-4-2(ESD) ±20KV(Contact)
 - IEC 61000-4-2(ESD) ±30KV(Air)
 - IEC 61000-4-4(EFT)40A(5/50ns)
 - Cable Discharge Event (CDE)
- ✧ Package optimized for high-speed lines
- ✧ Ultra-small package(2.5mm*1.0mm*0.5mm)
- ✧ Protects four data lines
- ✧ Low leakage current
- ✧ Low clamping voltage

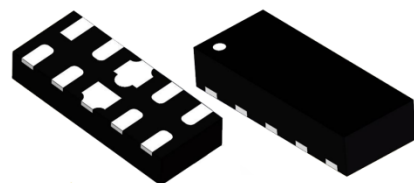
MACHANICAL DATA

- ✧ DFN2510 package
- ✧ Flammability Rating: UL 94V-0
- ✧ High temperature soldering guaranteed: 260°C/10s
- ✧ Reel size: 7 inch

APPLICATIONS

- ✧ USB Type-C
- ✧ High-speed data lines
- ✧ CAN bus

PACKAGE OUTLINE



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
P _{PP}	Peak Pulse Power (8/20μs)	140	W
V _{ESD}	ESD per IEC 61000-4-2 (Contact) ESD per IEC 61000-4-2 (Air)	±20 ±30	kV
T _{OPT}	Operating Temperature	-55/+125	°C
T _{STG}	Storage Temperature	-55/+150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V _{RWM}	Reverse Working Voltage	Any I/O pin to GND			24	V
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA Any I/O pin to GND	26			V
I _R	Reverse Leakage Current	V _{RWM} = 24V Any I/O pin to GND			0.5	μA
V _C	Clamping Voltage	I _{PP} = 2.8A, t _p = 8/20μs Any I/O pin to GND			50	V
C _{ESD}	Parasitic Capacitance	V _R = 0V, f = 1MHz Between I/O and GND		8	15	pF

Note: I/O pins are pin 1/2/4/5; GND pins are pin 3/8; pin 6/7/9/10 are NC and can be connected with any pin.

ELECTRICAL CHARACTERISTICS CURVE

Fig 1 8/20 μ s Waveform per IEC61000-4-5

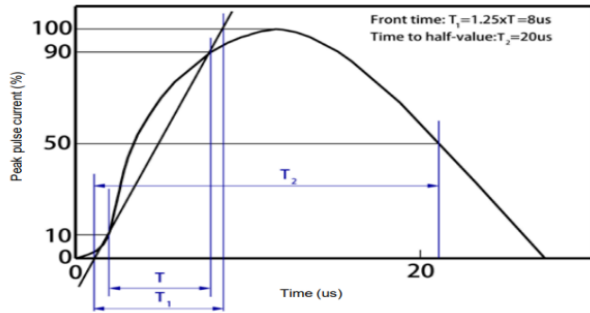


Fig 2 Contact Discharge Current Waveform per IEC 61000-4-2)

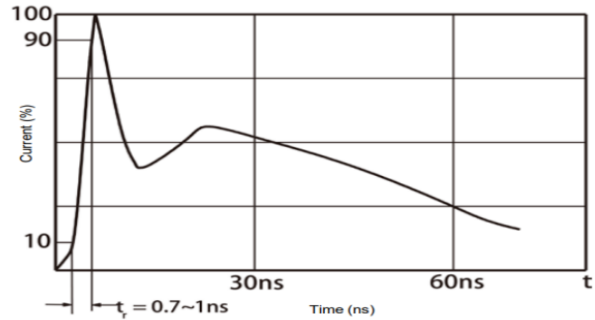


Fig 3 Voltage vs Capacitance

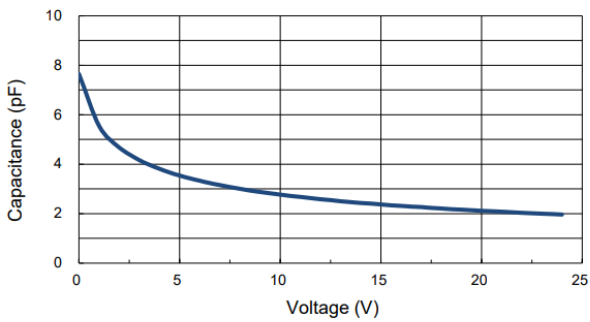
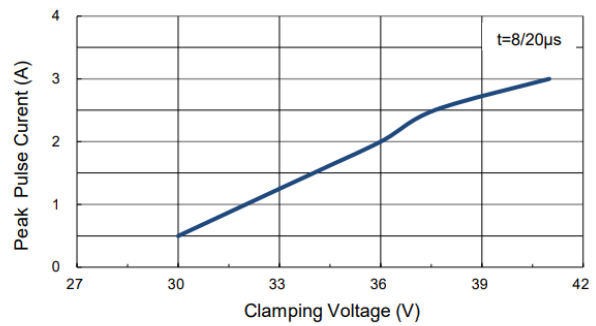
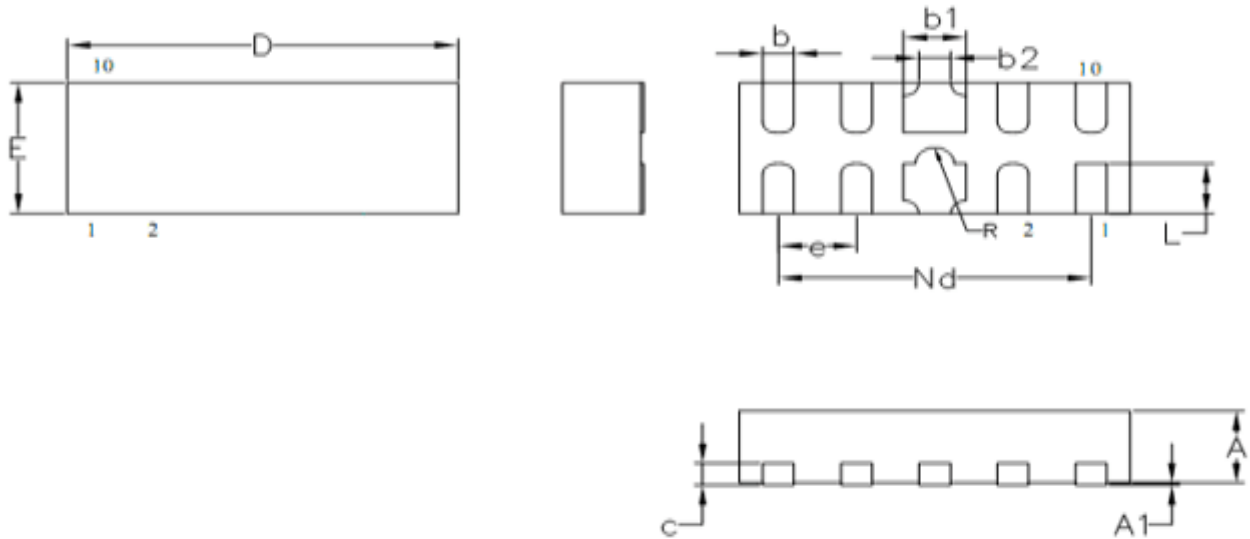


Fig 4 Clamping Voltage vs Peak Pulse Current



DFN2510 PACKAGE OUTLINE DIMENSIONS


Symbol	Dimensions (mm)		
	Min.	Nom.	Max.
D	2.45	2.50	2.55
E	0.95	1.00	1.05
b1	0.35	0.40	0.45
b2	0.20REF		
b	0.15	0.20	0.25
L	0.33	0.38	0.43
Nd	2.00BSC		
e	0.50BSC		
R	0.10	0.125	0.15
A	0.45	0.50	0.55
c	0.15REF		
A1	0.00	-	0.05